

AMENDMENTS TO THE ABSTRACT

Please replace the original Abstract with the following rewritten Abstract.

A semiconductor manufacturing device ~~according to the present invention~~ includes a processing chamber (11), a transferring passage (12) through which a wafer is put in and taken out of the processing chamber (11), an exhaust passage (13) and exhaust lines (40 and 40') through which a processing gas inside the processing chamber (11) is exhausted, and so on, and in order to heat the inner wall faces (11a, 11b, 12a, 13a, 410a, and 420a) of the processing chamber (11), the transferring passage (12), the exhaust passage (13) and the exhaust pipes (410 and 420), further includes sheet-like heating units (50, 60, 70, 80, 170, and 270) that sandwich and cover a thin plate-shaped resistive heating element by a pair of metal plates and cover the inner wall faces from the inner side. Thereby, the heating efficiency on the wall faces to be exposed to the processing gas increases, adhesion of by-products can be prevented, and deterioration of the resistive heating element can also be prevented.